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### What is "[Embedded - Microcontrollers](#)"?

"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

### Applications of "[Embedded - Microcontrollers](#)"

#### Details

Product Status	Obsolete
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I <sup>2</sup> C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	82
Program Memory Size	96KB (96K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	8K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 20x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	100-LQFP (14x20)
Purchase URL	<a href="https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f101pfdfa-v0">https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f101pfdfa-v0</a>

## ○ ROM, RAM capacities

Flash ROM	Data flash	RAM	RL78/G13					
			20 pins	24 pins	25 pins	30 pins	32 pins	36 pins
128 KB	8 KB	12 KB	—	—	—	R5F100AG	R5F100BG	R5F100CG
	—		—	—	—	R5F101AG	R5F101BG	R5F101CG
96 KB	8 KB	8 KB	—	—	—	R5F100AF	R5F100BF	R5F100CF
	—		—	—	—	R5F101AF	R5F101BF	R5F101CF
64 KB	4 KB	4 KB Note	R5F1006E	R5F1007E	R5F1008E	R5F100AE	R5F100BE	R5F100CE
	—		R5F1016E	R5F1017E	R5F1018E	R5F101AE	R5F101BE	R5F101CE
48 KB	4 KB	3 KB Note	R5F1006D	R5F1007D	R5F1008D	R5F100AD	R5F100BD	R5F100CD
	—		R5F1016D	R5F1017D	R5F1018D	R5F101AD	R5F101BD	R5F101CD
32 KB	4 KB	2 KB	R5F1006C	R5F1007C	R5F1008C	R5F100AC	R5F100BC	R5F100CC
	—		R5F1016C	R5F1017C	R5F1018C	R5F101AC	R5F101BC	R5F101CC
16 KB	4 KB	2 KB	R5F1006A	R5F1007A	R5F1008A	R5F100AA	R5F100BA	R5F100CA
	—		R5F1016A	R5F1017A	R5F1018A	R5F101AA	R5F101BA	R5F101CA

Flash ROM	Data flash	RAM	RL78/G13							
			40 pins	44 pins	48 pins	52 pins	64 pins	80 pins	100 pins	128 pins
512 KB	8 KB	32 KB Note	—	R5F100FL	R5F100GL	R5F100JL	R5F100LL	R5F100ML	R5F100PL	R5F100SL
	—		—	R5F101FL	R5F101GL	R5F101JL	R5F101LL	R5F101ML	R5F101PL	R5F101SL
384 KB	8 KB	24 KB	—	R5F100FK	R5F100GK	R5F100JK	R5F100LK	R5F100MK	R5F100PK	R5F100SK
	—		—	R5F101FK	R5F101GK	R5F101JK	R5F101LK	R5F101MK	R5F101PK	R5F101SK
256 KB	8 KB	20 KB Note	—	R5F100FJ	R5F100GJ	R5F100JJ	R5F100LJ	R5F100MJ	R5F100PJ	R5F100SJ
	—		—	R5F101FJ	R5F101GJ	R5F101JJ	R5F101LJ	R5F101MJ	R5F101PJ	R5F101SJ
192 KB	8 KB	16 KB	R5F100EH	R5F100FH	R5F100GH	R5F100JH	R5F100LH	R5F100MH	R5F100PH	R5F100SH
	—		R5F101EH	R5F101FH	R5F101GH	R5F101JH	R5F101LH	R5F101MH	R5F101PH	R5F101SH
128 KB	8 KB	12 KB	R5F100EG	R5F100FG	R5F100GG	R5F100JG	R5F100LG	R5F100MG	R5F100PG	—
	—		R5F101EG	R5F101FG	R5F101GG	R5F101JG	R5F101LG	R5F101MG	R5F101PG	—
96 KB	8 KB	8 KB	R5F100EF	R5F100FF	R5F100GF	R5F100JF	R5F100LF	R5F100MF	R5F100PF	—
	—		R5F101EF	R5F101FF	R5F101GF	R5F101JF	R5F101LF	R5F101MF	R5F101PF	—
64 KB	4 KB	4 KB Note	R5F100EE	R5F100FE	R5F100GE	R5F100JE	R5F100LE	—	—	—
	—		R5F101EE	R5F101FE	R5F101GE	R5F101JE	R5F101LE	—	—	—
48 KB	4 KB	3 KB Note	R5F100ED	R5F100FD	R5F100GD	R5F100JD	R5F100LD	—	—	—
	—		R5F101ED	R5F101FD	R5F101GD	R5F101JD	R5F101LD	—	—	—
32 KB	4 KB	2 KB	R5F100EC	R5F100FC	R5F100GC	R5F100JC	R5F100LC	—	—	—
	—		R5F101EC	R5F101FC	R5F101GC	R5F101JC	R5F101LC	—	—	—
16 KB	4 KB	2 KB	R5F100EA	R5F100FA	R5F100GA	—	—	—	—	—
	—		R5F101EA	R5F101FA	R5F101GA	—	—	—	—	—

**Note** The flash library uses RAM in self-programming and rewriting of the data flash memory.

The target products and start address of the RAM areas used by the flash library are shown below.

R5F100xD, R5F101xD (x = 6 to 8, A to C, E to G, J, L): Start address FF300H

R5F100xE, R5F101xE (x = 6 to 8, A to C, E to G, J, L): Start address FEF00H

R5F100xJ, R5F101xJ (x = F, G, J, L, M, P): Start address FAF00H

R5F100xL, R5F101xL (x = F, G, J, L, M, P, S): Start address F7F00H

For the RAM areas used by the flash library, see **Self RAM list of Flash Self-Programming Library for RL78 Family (R20UT2944)**.

Table 1-1. List of Ordering Part Numbers

(11/12)

Pin count	Package	Data flash	Fields of Application Note	Ordering Part Number
100 pins	100-pin plastic LFQFP (14 × 14 mm, 0.5 mm pitch)	Mounted	A	R5F100PFAFB#V0, R5F100PGAFA#V0, R5F100PHAFA#V0, R5F100PJAFB#V0, R5F100PKAFB#V0, R5F100PLAFB#V0 R5F100PFAFB#X0, R5F100PGAFA#X0, R5F100PHAFA#X0, R5F100PJAFB#X0, R5F100PKAFB#X0, R5F100PLAFB#X0
			D	R5F100PFDFB#V0, R5F100PGDFB#V0, R5F100PHDFB#V0, R5F100PJDFB#V0, R5F100PKDFB#V0, R5F100PLDFB#V0 R5F100PFDFB#X0, R5F100PGDFB#X0, R5F100PHDFB#X0, R5F100PJDFB#X0, R5F100PKDFB#X0, R5F100PLDFB#X0
			G	R5F100PFGFB#V0, R5F100PGGFB#V0, R5F100PHGFB#V0, R5F100PJGFB#V0 R5F100PFGFB#X0, R5F100PGGFB#X0, R5F100PHGFB#X0, R5F100PJGFB#X0
		Not mounted	A	R5F101PFAFB#V0, R5F101PGAFA#V0, R5F101PHAFA#V0, R5F101PJAFB#V0, R5F101PKAFB#V0, R5F101PLAFB#V0 R5F101PFAFB#X0, R5F101PGAFA#X0, R5F101PHAFA#X0, R5F101PJAFB#X0, R5F101PKAFB#X0, R5F101PLAFB#X0
	100-pin plastic LQFP (14 × 20 mm, 0.65 mm pitch)	Mounted	A	R5F100PFAFA#V0, R5F100PGAFA#V0, R5F100PHAFA#V0, R5F100PJAFB#V0, R5F100PKAFA#V0, R5F100PLAFA#V0 R5F100PFAFA#X0, R5F100PGAFA#X0, R5F100PHAFA#X0, R5F100PJAFB#X0, R5F100PKAFA#X0, R5F100PLAFA#X0
			D	R5F100PFDA#V0, R5F100PGDA#V0, R5F100PHDA#V0, R5F100PJDA#V0, R5F100PKDA#V0, R5F100PLDA#V0 R5F100PFDA#X0, R5F100PGDA#X0, R5F100PHDA#X0, R5F100PJDA#X0, R5F100PKDA#X0, R5F100PLDA#X0
			G	R5F100PFGFA#V0, R5F100PGGFA#V0, R5F100PHGFA#V0, R5F100PJGFA#V0 R5F100PFGFA#X0, R5F100PGGFA#X0, R5F100PHGFA#X0, R5F100PJGFA#X0
		Not mounted	A	R5F101PFAFA#V0, R5F101PGAFA#V0, R5F101PHAFA#V0, R5F101PJAFB#V0, R5F101PKAFA#V0, R5F101PLAFA#V0 R5F101PFAFA#X0, R5F101PGAFA#X0, R5F101PHAFA#X0, R5F101PJAFB#X0, R5F101PKAFA#X0, R5F101PLAFA#X0
			D	R5F101PFDA#V0, R5F101PGDA#V0, R5F101PHDA#V0, R5F101PJDA#V0, R5F101PKDA#V0, R5F101PLDA#V0 R5F101PFDA#X0, R5F101PGDA#X0, R5F101PHDA#X0, R5F101PJDA#X0, R5F101PKDA#X0, R5F101PLDA#X0

**Note** For the fields of application, refer to **Figure 1-1 Part Number, Memory Size, and Package of RL78/G13**.

**Caution** The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.

Table 1-1. List of Ordering Part Numbers

(12/12)

Pin count	Package	Data flash	Fields of Application <sup>Note</sup>	Ordering Part Number
128 pins	128-pin plastic LFQFP (14 × 20 mm, 0.5 mm pitch)	Mounted	A	R5F100SHAFB#V0, R5F100SJAFB#V0, R5F100SKAFB#V0, R5F100SLAFB#V0
			D	R5F100SHAFB#X0, R5F100SJAFB#X0, R5F100SKAFB#X0, R5F100SLAFB#X0 R5F100SHDFB#V0, R5F100SJDFB#V0, R5F100SKDFB#V0, R5F100SLDFB#V0 R5F100SHDFB#X0, R5F100SJDFB#X0, R5F100SKDFB#X0, R5F100SLDFB#X0
		Not mounted	A	R5F101SHAFB#V0, R5F101SJAFB#V0, R5F101SKAFB#V0, R5F101SLAFB#V0
			D	R5F101SHAFB#X0, R5F101SJAFB#X0, R5F101SKAFB#X0, R5F101SLAFB#X0 R5F101SHDFB#V0, R5F101SJDFB#V0, R5F101SKDFB#V0, R5F101SLDFB#V0 R5F101SHDFB#X0, R5F101SJDFB#X0, R5F101SKDFB#X0, R5F101SLDFB#X0

**Note** For the fields of application, refer to **Figure 1-1 Part Number, Memory Size, and Package of RL78/G13**.

**Caution** The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.

- Notes**
1. Total current flowing into  $V_{DD}$ ,  $EV_{DD0}$ , and  $EV_{DD1}$ , including the input leakage current flowing when the level of the input pin is fixed to  $V_{DD}$ ,  $EV_{DD0}$ , and  $EV_{DD1}$ , or  $V_{SS}$ ,  $EV_{SS0}$ , and  $EV_{SS1}$ . The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
  2. During HALT instruction execution by flash memory.
  3. When high-speed on-chip oscillator and subsystem clock are stopped.
  4. When high-speed system clock and subsystem clock are stopped.
  5. When high-speed on-chip oscillator and high-speed system clock are stopped. When  $RTCLPC = 1$  and setting ultra-low current consumption ( $AMPHS1 = 1$ ). The current flowing into the RTC is included. However, not including the current flowing into the 12-bit interval timer and watchdog timer.
  6. Not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
  7. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.
    - HS (high-speed main) mode:  $2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}$  @ 1 MHz to 32 MHz
    - $2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$  @ 1 MHz to 16 MHz
    - LS (low-speed main) mode:  $1.8\text{ V} \leq V_{DD} \leq 5.5\text{ V}$  @ 1 MHz to 8 MHz
    - LV (low-voltage main) mode:  $1.6\text{ V} \leq V_{DD} \leq 5.5\text{ V}$  @ 1 MHz to 4 MHz
  8. Regarding the value for current to operate the subsystem clock in STOP mode, refer to that in HALT mode.

- Remarks 1.** f<sub>MX</sub>: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
2. f<sub>IH</sub>: High-speed on-chip oscillator clock frequency
3. f<sub>SUB</sub>: Subsystem clock frequency (XT1 clock oscillation frequency)
4. Except subsystem clock operation and STOP mode, temperature condition of the TYP. value is T<sub>A</sub> = 25°C

**(3) 128-pin products, and flash ROM: 384 to 512 KB of 44- to 100-pin products****(T<sub>A</sub> = -40 to +85°C, 1.6 V ≤ EV<sub>DD0</sub> = EV<sub>DD1</sub> ≤ V<sub>DD</sub> ≤ 5.5 V, V<sub>SS</sub> = EV<sub>SS0</sub> = EV<sub>SS1</sub> = 0 V) (2/2)**

Parameter	Symbol				Conditions	MIN.	TYP.	MAX.	Unit	
Supply current Note 1	I <sub>DD2</sub> Note 2	HALT mode	HS (high-speed main) mode Note 7	f <sub>IH</sub> = 32 MHz <sup>Note 4</sup>	V <sub>DD</sub> = 5.0 V		0.62	1.89	mA	
					V <sub>DD</sub> = 3.0 V		0.62	1.89	mA	
				f <sub>IH</sub> = 24 MHz <sup>Note 4</sup>	V <sub>DD</sub> = 5.0 V		0.50	1.48	mA	
					V <sub>DD</sub> = 3.0 V		0.50	1.48	mA	
				f <sub>IH</sub> = 16 MHz <sup>Note 4</sup>	V <sub>DD</sub> = 5.0 V		0.44	1.12	mA	
					V <sub>DD</sub> = 3.0 V		0.44	1.12	mA	
			LS (low-speed main) mode Note 7	f <sub>IH</sub> = 8 MHz <sup>Note 4</sup>	V <sub>DD</sub> = 3.0 V		290	620	μA	
					V <sub>DD</sub> = 2.0 V		290	620	μA	
			LV (low-voltage main) mode Note 7	f <sub>IH</sub> = 4 MHz <sup>Note 4</sup>	V <sub>DD</sub> = 3.0 V		460	700	μA	
					V <sub>DD</sub> = 2.0 V		460	700	μA	
			HS (high-speed main) mode Note 7	f <sub>MX</sub> = 20 MHz <sup>Note 3</sup> , V <sub>DD</sub> = 5.0 V	Square wave input		0.31	1.14	mA	
					Resonator connection		0.48	1.34	mA	
				f <sub>MX</sub> = 20 MHz <sup>Note 3</sup> , V <sub>DD</sub> = 3.0 V	Square wave input		0.31	1.14	mA	
					Resonator connection		0.48	1.34	mA	
				f <sub>MX</sub> = 10 MHz <sup>Note 3</sup> , V <sub>DD</sub> = 5.0 V	Square wave input		0.21	0.68	mA	
					Resonator connection		0.28	0.76	mA	
				f <sub>MX</sub> = 10 MHz <sup>Note 3</sup> , V <sub>DD</sub> = 3.0 V	Square wave input		0.21	0.68	mA	
					Resonator connection		0.28	0.76	mA	
			LS (low-speed main) mode Note 7	f <sub>MX</sub> = 8 MHz <sup>Note 3</sup> , V <sub>DD</sub> = 3.0 V	Square wave input		110	390	μA	
					Resonator connection		160	450	μA	
				f <sub>MX</sub> = 8 MHz <sup>Note 3</sup> , V <sub>DD</sub> = 2.0 V	Square wave input		110	390	μA	
					Resonator connection		160	450	μA	
			Subsystem clock operation	f <sub>SUB</sub> = 32.768 kHz <sup>Note 5</sup> T <sub>A</sub> = −40°C	Square wave input		0.31	0.66	μA	
					Resonator connection		0.50	0.85	μA	
				f <sub>SUB</sub> = 32.768 kHz <sup>Note 5</sup> T <sub>A</sub> = +25°C	Square wave input		0.38	0.66	μA	
					Resonator connection		0.57	0.85	μA	
				f <sub>SUB</sub> = 32.768 kHz <sup>Note 5</sup> T <sub>A</sub> = +50°C	Square wave input		0.47	3.49	μA	
					Resonator connection		0.66	3.68	μA	
				f <sub>SUB</sub> = 32.768 kHz <sup>Note 5</sup> T <sub>A</sub> = +70°C	Square wave input		0.80	6.10	μA	
					Resonator connection		0.99	6.29	μA	
			f <sub>SUB</sub> = 32.768 kHz <sup>Note 5</sup> T <sub>A</sub> = +85°C	Square wave input		1.52	10.46	μA		
				Resonator connection		1.71	10.65	μA		
	I <sub>DD3</sub> Note 6	STOP mode Note 8	T <sub>A</sub> = −40°C					0.19	0.54	μA
			T <sub>A</sub> = +25°C					0.26	0.54	μA
			T <sub>A</sub> = +50°C					0.35	3.37	μA
			T <sub>A</sub> = +70°C					0.68	5.98	μA
			T <sub>A</sub> = +85°C					1.40	10.34	μA

(Notes and Remarks are listed on the next page.)

**(4) Peripheral Functions (Common to all products)****(T<sub>A</sub> = -40 to +85°C, 1.6 V ≤ EV<sub>DD0</sub> = EV<sub>DD1</sub> ≤ V<sub>DD</sub> ≤ 5.5 V, V<sub>SS</sub> = EV<sub>SS0</sub> = EV<sub>SS1</sub> = 0 V)**

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Low-speed on-chip oscillator operating current	I <sub>FIL</sub> <sup>Note 1</sup>				0.20		μA
RTC operating current	I <sub>RTC</sub> <sup>Notes 1, 2, 3</sup>				0.02		μA
12-bit interval timer operating current	I <sub>IT</sub> <sup>Notes 1, 2, 4</sup>				0.02		μA
Watchdog timer operating current	I <sub>WDT</sub> <sup>Notes 1, 2, 5</sup>	f <sub>IL</sub> = 15 kHz			0.22		μA
A/D converter operating current	I <sub>ADC</sub> <sup>Notes 1, 6</sup>	When conversion at maximum speed	Normal mode, AV <sub>REFP</sub> = V <sub>DD</sub> = 5.0 V		1.3	1.7	mA
			Low voltage mode, AV <sub>REFP</sub> = V <sub>DD</sub> = 3.0 V		0.5	0.7	mA
A/D converter reference voltage current	I <sub>ADREF</sub> <sup>Note 1</sup>				75.0		μA
Temperature sensor operating current	I <sub>TMPS</sub> <sup>Note 1</sup>				75.0		μA
LVD operating current	I <sub>LVI</sub> <sup>Notes 1, 7</sup>				0.08		μA
Self-programming operating current	I <sub>FSP</sub> <sup>Notes 1, 9</sup>				2.50	12.20	mA
BGO operating current	I <sub>BGO</sub> <sup>Notes 1, 8</sup>				2.50	12.20	mA
SNOOZE operating current	I <sub>SNOZ</sub> <sup>Note 1</sup>	ADC operation	The mode is performed <sup>Note 10</sup>		0.50	0.60	mA
			The A/D conversion operations are performed, Low voltage mode, AV <sub>REFP</sub> = V <sub>DD</sub> = 3.0 V		1.20	1.44	mA
		CSI/UART operation			0.70	0.84	mA

**Notes** 1. Current flowing to V<sub>DD</sub>.

- When high speed on-chip oscillator and high-speed system clock are stopped.
- Current flowing only to the real-time clock (RTC) (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either I<sub>DD1</sub> or I<sub>DD2</sub>, and I<sub>RTC</sub>, when the real-time clock operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, I<sub>FIL</sub> should be added. I<sub>DD2</sub> subsystem clock operation includes the operational current of the real-time clock.
- Current flowing only to the 12-bit interval timer (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either I<sub>DD1</sub> or I<sub>DD2</sub>, and I<sub>IT</sub>, when the 12-bit interval timer operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, I<sub>FIL</sub> should be added.
- Current flowing only to the watchdog timer (including the operating current of the low-speed on-chip oscillator). The supply current of the RL78 microcontrollers is the sum of I<sub>DD1</sub>, I<sub>DD2</sub> or I<sub>DD3</sub> and I<sub>WDT</sub> when the watchdog timer is in operation.

**Note** The following conditions are required for low voltage interface when  $E_{VDD0} < V_{DD}$

$1.8\text{ V} \leq E_{VDD0} < 2.7\text{ V}$  : MIN. 125 ns

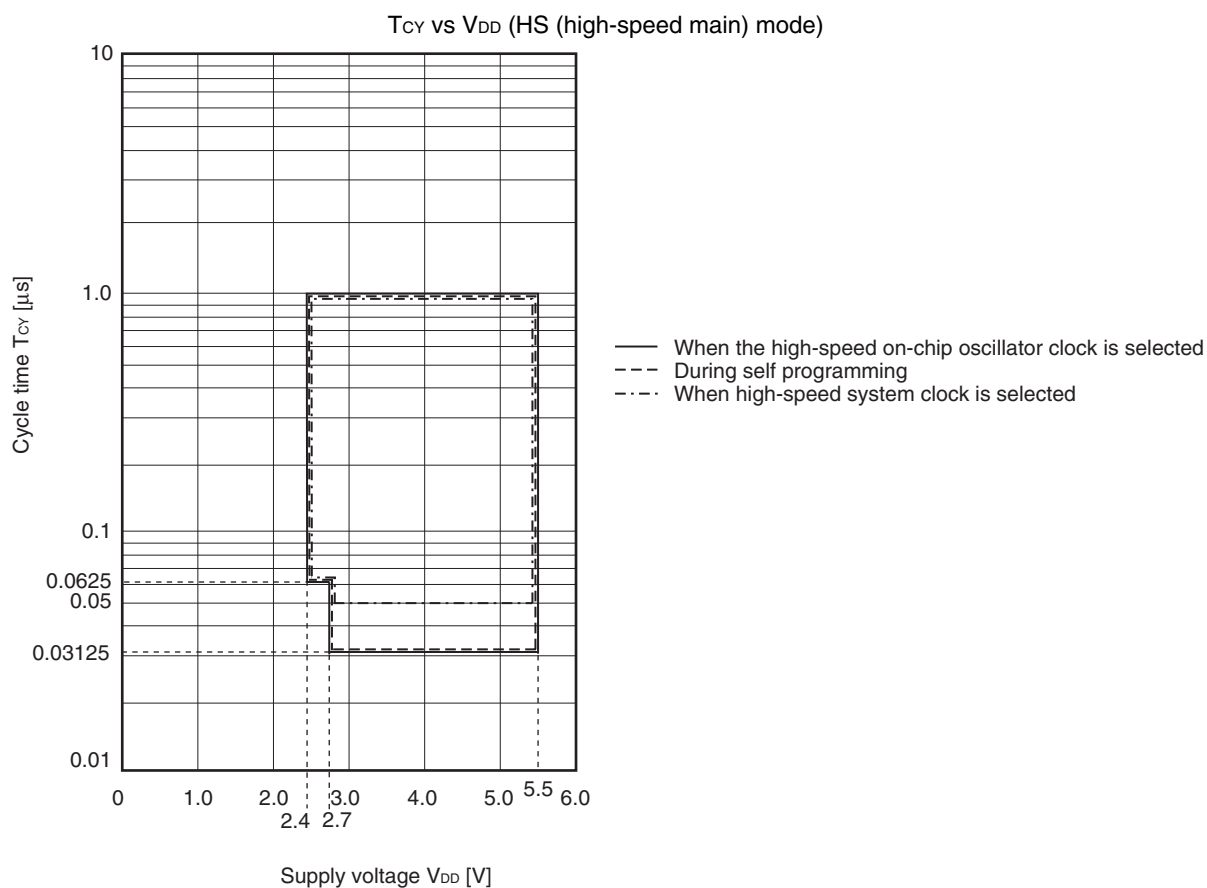
$1.6\text{ V} \leq E_{VDD0} < 1.8\text{ V}$  : MIN. 250 ns

**Remark**  $f_{MCK}$ : Timer array unit operation clock frequency

(Operation clock to be set by the CKSmn0, CKSmn1 bits of timer mode register mn (TMRmn).

m: Unit number ( $m = 0, 1$ ), n: Channel number ( $n = 0$  to  $7$ ))

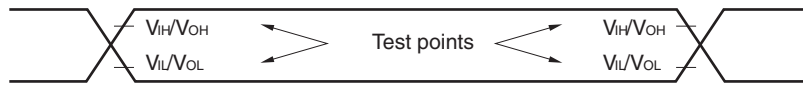
### Minimum Instruction Execution Time during Main System Clock Operation





## 2.5 Peripheral Functions Characteristics

### AC Timing Test Points



### 2.5.1 Serial array unit

#### (1) During communication at same potential (UART mode)

(T<sub>A</sub> = -40 to +85°C, 1.6 V ≤ E<sub>VDD0</sub> = E<sub>VDD1</sub> ≤ V<sub>DD</sub> ≤ 5.5 V, V<sub>SS</sub> = E<sub>VSS0</sub> = E<sub>VSS1</sub> = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Transfer rate <sup>Note 1</sup>		2.4 V ≤ E <sub>VDD0</sub> ≤ 5.5 V		f <sub>MCK</sub> /6 <sup>Note 2</sup>		f <sub>MCK</sub> /6		f <sub>MCK</sub> /6	bps
		Theoretical value of the maximum transfer rate f <sub>MCK</sub> = f <sub>CLK</sub> <sup>Note 3</sup>		5.3		1.3		0.6	Mbps
		1.8 V ≤ E <sub>VDD0</sub> ≤ 5.5 V		f <sub>MCK</sub> /6 <sup>Note 2</sup>		f <sub>MCK</sub> /6		f <sub>MCK</sub> /6	bps
		Theoretical value of the maximum transfer rate f <sub>MCK</sub> = f <sub>CLK</sub> <sup>Note 3</sup>		5.3		1.3		0.6	Mbps
		1.7 V ≤ E <sub>VDD0</sub> ≤ 5.5 V		f <sub>MCK</sub> /6 <sup>Note 2</sup>		f <sub>MCK</sub> /6 <sup>Note 2</sup>		f <sub>MCK</sub> /6	bps
		Theoretical value of the maximum transfer rate f <sub>MCK</sub> = f <sub>CLK</sub> <sup>Note 3</sup>		5.3		1.3		0.6	Mbps
		1.6 V ≤ E <sub>VDD0</sub> ≤ 5.5 V	—			f <sub>MCK</sub> /6 <sup>Note 2</sup>		f <sub>MCK</sub> /6	bps
		Theoretical value of the maximum transfer rate f <sub>MCK</sub> = f <sub>CLK</sub> <sup>Note 3</sup>	—			1.3		0.6	Mbps

**Notes 1.** Transfer rate in the SNOOZE mode is 4800 bps only.

**2.** The following conditions are required for low voltage interface when E<sub>VDD0</sub> < V<sub>DD</sub>.

2.4 V ≤ E<sub>VDD0</sub> < 2.7 V : MAX. 2.6 Mbps

1.8 V ≤ E<sub>VDD0</sub> < 2.4 V : MAX. 1.3 Mbps

1.6 V ≤ E<sub>VDD0</sub> < 1.8 V : MAX. 0.6 Mbps

**3.** The maximum operating frequencies of the CPU/peripheral hardware clock (f<sub>CLK</sub>) are:

HS (high-speed main) mode: 32 MHz (2.7 V ≤ V<sub>DD</sub> ≤ 5.5 V)

16 MHz (2.4 V ≤ V<sub>DD</sub> ≤ 5.5 V)

LS (low-speed main) mode: 8 MHz (1.8 V ≤ V<sub>DD</sub> ≤ 5.5 V)

LV (low-voltage main) mode: 4 MHz (1.6 V ≤ V<sub>DD</sub> ≤ 5.5 V)

**Caution** Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

**(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output)**  
**(2/3)**

(T<sub>A</sub> = -40 to +85°C, 1.8 V ≤ EV<sub>DD0</sub> = EV<sub>DD1</sub> ≤ V<sub>DD</sub> ≤ 5.5 V, V<sub>SS</sub> = EV<sub>SS0</sub> = EV<sub>SS1</sub> = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Slp setup time (to SCKp↑) <sup>Note 1</sup>	t <sub>SIK1</sub>	4.0 V ≤ EV <sub>DD0</sub> ≤ 5.5 V, 2.7 V ≤ V <sub>b</sub> ≤ 4.0 V, C <sub>b</sub> = 30 pF, R <sub>b</sub> = 1.4 kΩ	81		479		479		ns
		2.7 V ≤ EV <sub>DD0</sub> < 4.0 V, 2.3 V ≤ V <sub>b</sub> ≤ 2.7 V, C <sub>b</sub> = 30 pF, R <sub>b</sub> = 2.7 kΩ	177		479		479		ns
		1.8 V ≤ EV <sub>DD0</sub> < 3.3 V, 1.6 V ≤ V <sub>b</sub> ≤ 2.0 V <sup>Note 2</sup> , C <sub>b</sub> = 30 pF, R <sub>b</sub> = 5.5 kΩ	479		479		479		ns
Slp hold time (from SCKp↑) <sup>Note 1</sup>	t <sub>KSH1</sub>	4.0 V ≤ EV <sub>DD0</sub> ≤ 5.5 V, 2.7 V ≤ V <sub>b</sub> ≤ 4.0 V, C <sub>b</sub> = 30 pF, R <sub>b</sub> = 1.4 kΩ	19		19		19		ns
		2.7 V ≤ EV <sub>DD0</sub> < 4.0 V, 2.3 V ≤ V <sub>b</sub> ≤ 2.7 V, C <sub>b</sub> = 30 pF, R <sub>b</sub> = 2.7 kΩ	19		19		19		ns
		1.8 V ≤ EV <sub>DD0</sub> < 3.3 V, 1.6 V ≤ V <sub>b</sub> ≤ 2.0 V <sup>Note 2</sup> , C <sub>b</sub> = 30 pF, R <sub>b</sub> = 5.5 kΩ	19		19		19		ns
Delay time from SCKp↓ to SOp output <sup>Note 1</sup>	t <sub>KSO1</sub>	4.0 V ≤ EV <sub>DD0</sub> ≤ 5.5 V, 2.7 V ≤ V <sub>b</sub> ≤ 4.0 V, C <sub>b</sub> = 30 pF, R <sub>b</sub> = 1.4 kΩ		100		100		100	ns
		2.7 V ≤ EV <sub>DD0</sub> < 4.0 V, 2.3 V ≤ V <sub>b</sub> ≤ 2.7 V, C <sub>b</sub> = 30 pF, R <sub>b</sub> = 2.7 kΩ		195		195		195	ns
		1.8 V ≤ EV <sub>DD0</sub> < 3.3 V, 1.6 V ≤ V <sub>b</sub> ≤ 2.0 V <sup>Note 2</sup> , C <sub>b</sub> = 30 pF, R <sub>b</sub> = 5.5 kΩ		483		483		483	ns

- Notes**
1. When DAP<sub>mn</sub> = 0 and CKP<sub>mn</sub> = 0, or DAP<sub>mn</sub> = 1 and CKP<sub>mn</sub> = 1.
  2. Use it with EV<sub>DD0</sub> ≥ V<sub>b</sub>.

**Caution** Select the TTL input buffer for the Slp pin and the N-ch open drain output (V<sub>DD</sub> tolerance (When 20- to 52-pin products)/EV<sub>DD</sub> tolerance (When 64- to 128-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V<sub>IH</sub> and V<sub>IL</sub>, see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the page after the next page.)

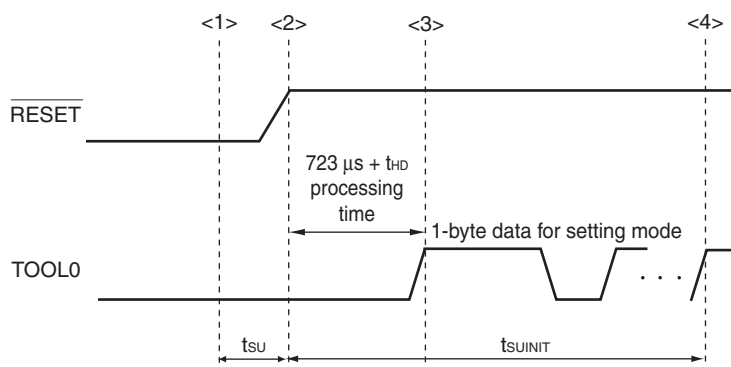
**(10) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I<sup>2</sup>C mode) (1/2)****(T<sub>A</sub> = -40 to +85°C, 1.8 V ≤ EV<sub>DD0</sub> = EV<sub>DD1</sub> ≤ V<sub>DD</sub> ≤ 5.5 V, V<sub>SS</sub> = EV<sub>SS0</sub> = EV<sub>SS1</sub> = 0 V)**

Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLr clock frequency	f <sub>SCL</sub>	4.0 V ≤ EV <sub>DD0</sub> ≤ 5.5 V, 2.7 V ≤ V <sub>b</sub> ≤ 4.0 V, C <sub>b</sub> = 50 pF, R <sub>b</sub> = 2.7 kΩ		1000 Note 1		300 Note 1		300 Note 1	kHz
		2.7 V ≤ EV <sub>DD0</sub> < 4.0 V, 2.3 V ≤ V <sub>b</sub> ≤ 2.7 V, C <sub>b</sub> = 50 pF, R <sub>b</sub> = 2.7 kΩ		1000 Note 1		300 Note 1		300 Note 1	kHz
		4.0 V ≤ EV <sub>DD0</sub> ≤ 5.5 V, 2.7 V ≤ V <sub>b</sub> ≤ 4.0 V, C <sub>b</sub> = 100 pF, R <sub>b</sub> = 2.8 kΩ		400 Note 1		300 Note 1		300 Note 1	kHz
		2.7 V ≤ EV <sub>DD0</sub> < 4.0 V, 2.3 V ≤ V <sub>b</sub> ≤ 2.7 V, C <sub>b</sub> = 100 pF, R <sub>b</sub> = 2.7 kΩ		400 Note 1		300 Note 1		300 ote 1	kHz
		1.8 V ≤ EV <sub>DD0</sub> < 3.3 V, 1.6 V ≤ V <sub>b</sub> ≤ 2.0 V <sup>Note 2</sup> , C <sub>b</sub> = 100 pF, R <sub>b</sub> = 5.5 kΩ		300 Note 1		300 Note 1		300 Note 1	kHz
Hold time when SCLr = "L"	t <sub>LOW</sub>	4.0 V ≤ EV <sub>DD0</sub> ≤ 5.5 V, 2.7 V ≤ V <sub>b</sub> ≤ 4.0 V, C <sub>b</sub> = 50 pF, R <sub>b</sub> = 2.7 kΩ	475		1550		1550		ns
		2.7 V ≤ EV <sub>DD0</sub> < 4.0 V, 2.3 V ≤ V <sub>b</sub> ≤ 2.7 V, C <sub>b</sub> = 50 pF, R <sub>b</sub> = 2.7 kΩ	475		1550		1550		ns
		4.0 V ≤ EV <sub>DD0</sub> ≤ 5.5 V, 2.7 V ≤ V <sub>b</sub> ≤ 4.0 V, C <sub>b</sub> = 100 pF, R <sub>b</sub> = 2.8 kΩ	1150		1550		1550		ns
		2.7 V ≤ EV <sub>DD0</sub> < 4.0 V, 2.3 V ≤ V <sub>b</sub> ≤ 2.7 V, C <sub>b</sub> = 100 pF, R <sub>b</sub> = 2.7 kΩ	1150		1550		1550		ns
		1.8 V ≤ EV <sub>DD0</sub> < 3.3 V, 1.6 V ≤ V <sub>b</sub> ≤ 2.0 V <sup>Note 2</sup> , C <sub>b</sub> = 100 pF, R <sub>b</sub> = 5.5 kΩ	1550		1550		1550		ns
Hold time when SCLr = "H"	t <sub>HIGH</sub>	4.0 V ≤ EV <sub>DD0</sub> ≤ 5.5 V, 2.7 V ≤ V <sub>b</sub> ≤ 4.0 V, C <sub>b</sub> = 50 pF, R <sub>b</sub> = 2.7 kΩ	245		610		610		ns
		2.7 V ≤ EV <sub>DD0</sub> < 4.0 V, 2.3 V ≤ V <sub>b</sub> ≤ 2.7 V, C <sub>b</sub> = 50 pF, R <sub>b</sub> = 2.7 kΩ	200		610		610		ns
		4.0 V ≤ EV <sub>DD0</sub> ≤ 5.5 V, 2.7 V ≤ V <sub>b</sub> ≤ 4.0 V, C <sub>b</sub> = 100 pF, R <sub>b</sub> = 2.8 kΩ	675		610		610		ns
		2.7 V ≤ EV <sub>DD0</sub> < 4.0 V, 2.3 V ≤ V <sub>b</sub> ≤ 2.7 V, C <sub>b</sub> = 100 pF, R <sub>b</sub> = 2.7 kΩ	600		610		610		ns
		1.8 V ≤ EV <sub>DD0</sub> < 3.3 V, 1.6 V ≤ V <sub>b</sub> ≤ 2.0 V <sup>Note 2</sup> , C <sub>b</sub> = 100 pF, R <sub>b</sub> = 5.5 kΩ	610		610		610		ns

## 2.10 Timing of Entry to Flash Memory Programming Modes

( $T_A = -40$  to  $+85^\circ\text{C}$ ,  $1.8\text{ V} \leq \text{EV}_{\text{DD}0} = \text{EV}_{\text{DD}1} \leq V_{\text{DD}} \leq 5.5\text{ V}$ ,  $V_{\text{SS}} = \text{EV}_{\text{SS}0} = \text{EV}_{\text{SS}1} = 0\text{ V}$ )

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Time to complete the communication for the initial setting after the external reset is released	$t_{\text{SUINIT}}$	POR and LVD reset must be released before the external reset is released.			100	ms
Time to release the external reset after the TOOL0 pin is set to the low level	$t_{\text{SU}}$	POR and LVD reset must be released before the external reset is released.	10			$\mu\text{s}$
Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)	$t_{\text{HD}}$	POR and LVD reset must be released before the external reset is released.	1			ms



- <1> The low level is input to the TOOL0 pin.
- <2> The external reset is released (POR and LVD reset must be released before the external reset is released.).
- <3> The TOOL0 pin is set to the high level.
- <4> Setting of the flash memory programming mode by UART reception and complete the baud rate setting.

**Remark**  $t_{\text{SUINIT}}$ : Communication for the initial setting must be completed within 100 ms after the external reset is released during this period.

$t_{\text{SU}}$ : Time to release the external reset after the TOOL0 pin is set to the low level

$t_{\text{HD}}$ : Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)

### 3. ELECTRICAL SPECIFICATIONS (G: INDUSTRIAL APPLICATIONS $T_A = -40$ to $+105^\circ\text{C}$ )

This chapter describes the following electrical specifications.

Target products G: Industrial applications  $T_A = -40$  to  $+105^\circ\text{C}$   
R5F100xxGxx

- Cautions**
1. The RL78 microcontrollers have an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.
  2. With products not provided with an  $\text{EV}_{\text{DD0}}$ ,  $\text{EV}_{\text{DD1}}$ ,  $\text{EV}_{\text{SS0}}$ , or  $\text{EV}_{\text{SS1}}$  pin, replace  $\text{EV}_{\text{DD0}}$  and  $\text{EV}_{\text{DD1}}$  with  $V_{\text{DD}}$ , or replace  $\text{EV}_{\text{SS0}}$  and  $\text{EV}_{\text{SS1}}$  with  $V_{\text{SS}}$ .
  3. The pins mounted depend on the product. Refer to 2.1 Port Function to 2.2.1 Functions for each product.
  4. Please contact Renesas Electronics sales office for derating of operation under  $T_A = +85^\circ\text{C}$  to  $+105^\circ\text{C}$ . Derating is the systematic reduction of load for the sake of improved reliability.

**Remark** When RL78/G13 is used in the range of  $T_A = -40$  to  $+85^\circ\text{C}$ , see **CHAPTER 2 ELECTRICAL SPECIFICATIONS ( $T_A = -40$  to  $+85^\circ\text{C}$ )**.

There are following differences between the products "G: Industrial applications ( $T_A = -40$  to  $+105^\circ\text{C}$ )" and the products "A: Consumer applications, and D: Industrial applications".

Parameter	Application	
	A: Consumer applications, D: Industrial applications	G: Industrial applications
Operating ambient temperature	$T_A = -40$ to $+85^\circ\text{C}$	$T_A = -40$ to $+105^\circ\text{C}$
Operating mode Operating voltage range	HS (high-speed main) mode: $2.7\text{ V} \leq V_{\text{DD}} \leq 5.5\text{ V}@1\text{ MHz to }32\text{ MHz}$ $2.4\text{ V} \leq V_{\text{DD}} \leq 5.5\text{ V}@1\text{ MHz to }16\text{ MHz}$ LS (low-speed main) mode: $1.8\text{ V} \leq V_{\text{DD}} \leq 5.5\text{ V}@1\text{ MHz to }8\text{ MHz}$ LV (low-voltage main) mode: $1.6\text{ V} \leq V_{\text{DD}} \leq 5.5\text{ V}@1\text{ MHz to }4\text{ MHz}$	HS (high-speed main) mode only: $2.7\text{ V} \leq V_{\text{DD}} \leq 5.5\text{ V}@1\text{ MHz to }32\text{ MHz}$ $2.4\text{ V} \leq V_{\text{DD}} \leq 5.5\text{ V}@1\text{ MHz to }16\text{ MHz}$
High-speed on-chip oscillator clock accuracy	$1.8\text{ V} \leq V_{\text{DD}} \leq 5.5\text{ V}$ $\pm 1.0\% @ T_A = -20$ to $+85^\circ\text{C}$ $\pm 1.5\% @ T_A = -40$ to $-20^\circ\text{C}$ $1.6\text{ V} \leq V_{\text{DD}} < 1.8\text{ V}$ $\pm 5.0\% @ T_A = -20$ to $+85^\circ\text{C}$ $\pm 5.5\% @ T_A = -40$ to $-20^\circ\text{C}$	$2.4\text{ V} \leq V_{\text{DD}} \leq 5.5\text{ V}$ $\pm 2.0\% @ T_A = +85$ to $+105^\circ\text{C}$ $\pm 1.0\% @ T_A = -20$ to $+85^\circ\text{C}$ $\pm 1.5\% @ T_A = -40$ to $-20^\circ\text{C}$
Serial array unit	UART CSI: $f_{\text{CLK}}/2$ (supporting 16 Mbps), $f_{\text{CLK}}/4$ Simplified I <sup>2</sup> C communication	UART CSI: $f_{\text{CLK}}/4$ Simplified I <sup>2</sup> C communication
IICA	Normal mode Fast mode Fast mode plus	Normal mode Fast mode
Voltage detector	Rise detection voltage: 1.67 V to 4.06 V (14 levels) Fall detection voltage: 1.63 V to 3.98 V (14 levels)	Rise detection voltage: 2.61 V to 4.06 V (8 levels) Fall detection voltage: 2.55 V to 3.98 V (8 levels)

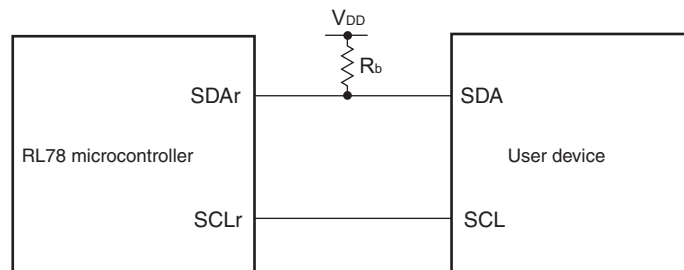
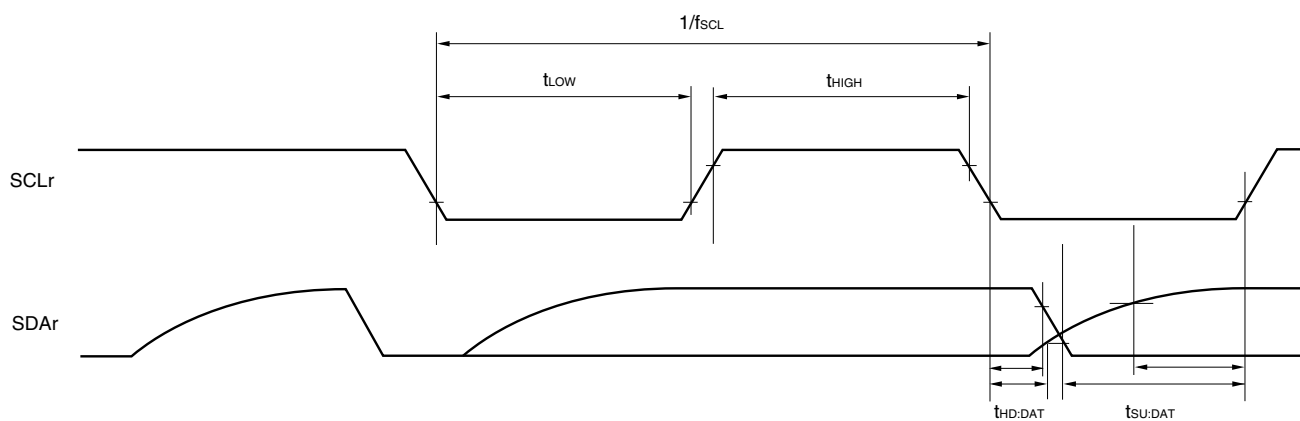
(Remark is listed on the next page.)

## (2) Flash ROM: 96 to 256 KB of 30- to 100-pin products

(TA =  $-40$  to  $+105^\circ\text{C}$ ,  $2.4\text{ V} \leq \text{EV}_{\text{DD}0} = \text{EV}_{\text{DD}1} \leq \text{V}_{\text{DD}} \leq 5.5\text{ V}$ ,  $\text{V}_{\text{SS}} = \text{EV}_{\text{SS}0} = \text{EV}_{\text{SS}1} = 0\text{ V}$ ) (2/2)

Parameter	Symbol	Conditions				MIN.	TYP.	MAX.	Unit	
Supply current Note 1	I <sub>DD2</sub> Note 2	HALT mode	HS (high-speed main) mode Note 7	f <sub>IH</sub> = 32 MHz <sup>Note 4</sup>	V <sub>DD</sub> = 5.0 V		0.62	3.40	mA	
					V <sub>DD</sub> = 3.0 V		0.62	3.40	mA	
				f <sub>IH</sub> = 24 MHz <sup>Note 4</sup>	V <sub>DD</sub> = 5.0 V		0.50	2.70	mA	
					V <sub>DD</sub> = 3.0 V		0.50	2.70	mA	
				f <sub>IH</sub> = 16 MHz <sup>Note 4</sup>	V <sub>DD</sub> = 5.0 V		0.44	1.90	mA	
					V <sub>DD</sub> = 3.0 V		0.44	1.90	mA	
				HS (high-speed main) mode Note 7	f <sub>MX</sub> = 20 MHz <sup>Note 3</sup> , V <sub>DD</sub> = 5.0 V	Square wave input		0.31	2.10	mA
						Resonator connection		0.48	2.20	mA
					f <sub>MX</sub> = 20 MHz <sup>Note 3</sup> , V <sub>DD</sub> = 3.0 V	Square wave input		0.31	2.10	mA
						Resonator connection		0.48	2.20	mA
			f <sub>MX</sub> = 10 MHz <sup>Note 3</sup> , V <sub>DD</sub> = 5.0 V		Square wave input		0.21	1.10	mA	
					Resonator connection		0.28	1.20	mA	
			f <sub>MX</sub> = 10 MHz <sup>Note 3</sup> , V <sub>DD</sub> = 3.0 V		Square wave input		0.21	1.10	mA	
					Resonator connection		0.28	1.20	mA	
			Subsystem clock operation	f <sub>SUB</sub> = 32.768 kHz <sup>Note 5</sup> T <sub>A</sub> = −40°C	Square wave input		0.28	0.61	μA	
					Resonator connection		0.47	0.80	μA	
				f <sub>SUB</sub> = 32.768 kHz <sup>Note 5</sup> T <sub>A</sub> = +25°C	Square wave input		0.34	0.61	μA	
					Resonator connection		0.53	0.80	μA	
				f <sub>SUB</sub> = 32.768 kHz <sup>Note 5</sup> T <sub>A</sub> = +50°C	Square wave input		0.41	2.30	μA	
					Resonator connection		0.60	2.49	μA	
				f <sub>SUB</sub> = 32.768 kHz <sup>Note 5</sup> T <sub>A</sub> = +70°C	Square wave input		0.64	4.03	μA	
					Resonator connection		0.83	4.22	μA	
				f <sub>SUB</sub> = 32.768 kHz <sup>Note 5</sup> T <sub>A</sub> = +85°C	Square wave input		1.09	8.04	μA	
					Resonator connection		1.28	8.23	μA	
			f <sub>SUB</sub> = 32.768 kHz <sup>Note 5</sup> T <sub>A</sub> = +105°C	Square wave input		5.50	41.00	μA		
				Resonator connection		5.50	41.00	μA		
	I <sub>DD3</sub> <sup>Note 6</sup>	STOP mode <sup>Note 8</sup>	T <sub>A</sub> = −40°C					0.19	0.52	μA
			T <sub>A</sub> = +25°C					0.25	0.52	μA
			T <sub>A</sub> = +50°C					0.32	2.21	μA
			T <sub>A</sub> = +70°C					0.55	3.94	μA
			T <sub>A</sub> = +85°C					1.00	7.95	μA
			T <sub>A</sub> = +105°C					5.00	40.00	μA

(Notes and Remarks are listed on the next page.)

**Simplified I<sup>2</sup>C mode connection diagram (during communication at same potential)****Simplified I<sup>2</sup>C mode serial transfer timing (during communication at same potential)**

- Remarks**
- $R_b[\Omega]$ : Communication line (SDAr) pull-up resistance,  $C_b[F]$ : Communication line (SDAr, SCLr) load capacitance
  - r: IIC number (r = 00, 01, 10, 11, 20, 21, 30, 31), g: PIM number (g = 0, 1, 4, 5, 8, 14),  
h: POM number (g = 0, 1, 4, 5, 7 to 9, 14)
  - $f_{MCK}$ : Serial array unit operation clock frequency  
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), mn = 00 to 03, 10 to 13)

**(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (2/3)****( $T_A = -40$  to  $+105^\circ\text{C}$ ,  $2.4\text{ V} \leq \text{EV}_{\text{DD}0} = \text{EV}_{\text{DD}1} \leq \text{V}_{\text{DD}} \leq 5.5\text{ V}$ ,  $\text{V}_{\text{SS}} = \text{EV}_{\text{SS}0} = \text{EV}_{\text{SS}1} = 0\text{ V}$ )**

Parameter	Symbol	Conditions	HS (high-speed main) Mode		Unit
			MIN.	MAX.	
Slp setup time (to SCKp $\uparrow$ ) <sup>Note</sup>	$t_{\text{SIK}1}$	$4.0\text{ V} \leq \text{EV}_{\text{DD}0} \leq 5.5\text{ V}$ , $2.7\text{ V} \leq \text{V}_b \leq 4.0\text{ V}$ , $\text{C}_b = 30\text{ pF}$ , $\text{R}_b = 1.4\text{ k}\Omega$	162		ns
		$2.7\text{ V} \leq \text{EV}_{\text{DD}0} < 4.0\text{ V}$ , $2.3\text{ V} \leq \text{V}_b \leq 2.7\text{ V}$ , $\text{C}_b = 30\text{ pF}$ , $\text{R}_b = 2.7\text{ k}\Omega$	354		ns
		$2.4\text{ V} \leq \text{EV}_{\text{DD}0} < 3.3\text{ V}$ , $1.6\text{ V} \leq \text{V}_b \leq 2.0\text{ V}$ , $\text{C}_b = 30\text{ pF}$ , $\text{R}_b = 5.5\text{ k}\Omega$	958		ns
Slp hold time (from SCKp $\uparrow$ ) <sup>Note</sup>	$t_{\text{KSI}1}$	$4.0\text{ V} \leq \text{EV}_{\text{DD}0} \leq 5.5\text{ V}$ , $2.7\text{ V} \leq \text{V}_b \leq 4.0\text{ V}$ , $\text{C}_b = 30\text{ pF}$ , $\text{R}_b = 1.4\text{ k}\Omega$	38		ns
		$2.7\text{ V} \leq \text{EV}_{\text{DD}0} < 4.0\text{ V}$ , $2.3\text{ V} \leq \text{V}_b \leq 2.7\text{ V}$ , $\text{C}_b = 30\text{ pF}$ , $\text{R}_b = 2.7\text{ k}\Omega$	38		ns
		$2.4\text{ V} \leq \text{EV}_{\text{DD}0} < 3.3\text{ V}$ , $1.6\text{ V} \leq \text{V}_b \leq 2.0\text{ V}$ , $\text{C}_b = 30\text{ pF}$ , $\text{R}_b = 2.7\text{ k}\Omega$	38		ns
Delay time from SCKp $\downarrow$ to SOp output <sup>Note</sup>	$t_{\text{KSO}1}$	$4.0\text{ V} \leq \text{EV}_{\text{DD}0} \leq 5.5\text{ V}$ , $2.7\text{ V} \leq \text{V}_b \leq 4.0\text{ V}$ , $\text{C}_b = 30\text{ pF}$ , $\text{R}_b = 1.4\text{ k}\Omega$		200	ns
		$2.7\text{ V} \leq \text{EV}_{\text{DD}0} < 4.0\text{ V}$ , $2.3\text{ V} \leq \text{V}_b \leq 2.7\text{ V}$ , $\text{C}_b = 30\text{ pF}$ , $\text{R}_b = 2.7\text{ k}\Omega$		390	ns
		$2.4\text{ V} \leq \text{EV}_{\text{DD}0} < 3.3\text{ V}$ , $1.6\text{ V} \leq \text{V}_b \leq 2.0\text{ V}$ , $\text{C}_b = 30\text{ pF}$ , $\text{R}_b = 5.5\text{ k}\Omega$		966	ns

**Note** When  $\text{DAPmn} = 0$  and  $\text{CKPmn} = 0$ , or  $\text{DAPmn} = 1$  and  $\text{CKPmn} = 1$ .

**Caution** Select the TTL input buffer for the Slp pin and the N-ch open drain output ( $\text{V}_{\text{DD}}$  tolerance (for the 20- to 52-pin products)/ $\text{EV}_{\text{DD}}$  tolerance (for the 64- to 100-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For  $\text{V}_{\text{IH}}$  and  $\text{V}_{\text{IL}}$ , see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the page after the next page.)



### 3.6 Analog Characteristics

#### 3.6.1 A/D converter characteristics

Classification of A/D converter characteristics

Input channel	Reference Voltage		
	Reference voltage (+) = $AV_{REFP}$ Reference voltage (-) = $AV_{REFM}$	Reference voltage (+) = $V_{DD}$ Reference voltage (-) = $V_{SS}$	Reference voltage (+) = $V_{BGR}$ Reference voltage (-) = $AV_{REFM}$
ANI0 to ANI14	Refer to 3.6.1 (1).	Refer to 3.6.1 (3).	Refer to 3.6.1 (4).
ANI16 to ANI26	Refer to 3.6.1 (2).		
Internal reference voltage Temperature sensor output voltage	Refer to 3.6.1 (1).		—

(1) When reference voltage (+) =  $AV_{REFP}/ANI0$  ( $ADREFP1 = 0$ ,  $ADREFP0 = 1$ ), reference voltage (-) =  $AV_{REFM}/ANI1$  ( $ADREFM = 1$ ), target pin : ANI2 to ANI14, internal reference voltage, and temperature sensor output voltage

( $T_A = -40$  to  $+105^\circ\text{C}$ ,  $2.4\text{ V} \leq AV_{REFP} \leq V_{DD} \leq 5.5\text{ V}$ ,  $V_{SS} = 0\text{ V}$ , Reference voltage (+) =  $AV_{REFP}$ , Reference voltage (-) =  $AV_{REFM} = 0\text{ V}$ )

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error <sup>Note 1</sup>	AINL	10-bit resolution $AV_{REFP} = V_{DD}$ <sup>Note 3</sup>	$2.4\text{ V} \leq AV_{REFP} \leq 5.5\text{ V}$		1.2	$\pm 3.5$	LSB
Conversion time	$t_{CONV}$	10-bit resolution Target pin: ANI2 to ANI14	$3.6\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	2.125		39	$\mu\text{s}$
			$2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	3.1875		39	$\mu\text{s}$
			$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	17		39	$\mu\text{s}$
		10-bit resolution Target pin: Internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	$3.6\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	2.375		39	$\mu\text{s}$
			$2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	3.5625		39	$\mu\text{s}$
			$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	17		39	$\mu\text{s}$
Zero-scale error <sup>Notes 1, 2</sup>	$E_{ZS}$	10-bit resolution $AV_{REFP} = V_{DD}$ <sup>Note 3</sup>	$2.4\text{ V} \leq AV_{REFP} \leq 5.5\text{ V}$			$\pm 0.25$	%FSR
Full-scale error <sup>Notes 1, 2</sup>	$E_{FS}$	10-bit resolution $AV_{REFP} = V_{DD}$ <sup>Note 3</sup>	$2.4\text{ V} \leq AV_{REFP} \leq 5.5\text{ V}$			$\pm 0.25$	%FSR
Integral linearity error <sup>Note 1</sup>	ILE	10-bit resolution $AV_{REFP} = V_{DD}$ <sup>Note 3</sup>	$2.4\text{ V} \leq AV_{REFP} \leq 5.5\text{ V}$			$\pm 2.5$	LSB
Differential linearity error <sup>Note 1</sup>	DLE	10-bit resolution $AV_{REFP} = V_{DD}$ <sup>Note 3</sup>	$2.4\text{ V} \leq AV_{REFP} \leq 5.5\text{ V}$			$\pm 1.5$	LSB
Analog input voltage	$V_{AIN}$	ANI2 to ANI14		0		$AV_{REFP}$	V
		Internal reference voltage output ( $2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$ , HS (high-speed main) mode)		$V_{BGR}$ <sup>Note 4</sup>			V
		Temperature sensor output voltage ( $2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$ , HS (high-speed main) mode)		$V_{TMPS25}$ <sup>Note 4</sup>			V

(Notes are listed on the next page.)

(3) When reference voltage (+) =  $V_{DD}$  (ADREFP1 = 0, ADREFP0 = 0), reference voltage (–) =  $V_{SS}$  (ADREFM = 0), target pin : ANI0 to ANI14, ANI16 to ANI26, internal reference voltage, and temperature sensor output voltage

( $T_A = -40$  to  $+105^\circ\text{C}$ ,  $2.4\text{ V} \leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq 5.5\text{ V}$ ,  $V_{SS} = EV_{SS0} = EV_{SS1} = 0\text{ V}$ , Reference voltage (+) =  $V_{DD}$ , Reference voltage (–) =  $V_{SS}$ )

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error <sup>Note 1</sup>	AINL	10-bit resolution	$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$		1.2	$\pm 7.0$	LSB
Conversion time	$t_{CONV}$	10-bit resolution Target pin: ANI0 to ANI14, ANI16 to ANI26	$3.6\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	2.125		39	$\mu\text{s}$
			$2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	3.1875		39	$\mu\text{s}$
			$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	17		39	$\mu\text{s}$
		10-bit resolution Target pin: Internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	$3.6\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	2.375		39	$\mu\text{s}$
			$2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	3.5625		39	$\mu\text{s}$
			$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	17		39	$\mu\text{s}$
Zero-scale error <sup>Notes 1, 2</sup>	E <sub>ZS</sub>	10-bit resolution	$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$			$\pm 0.60$	%FSR
Full-scale error <sup>Notes 1, 2</sup>	E <sub>FS</sub>	10-bit resolution	$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$			$\pm 0.60$	%FSR
Integral linearity error <sup>Note 1</sup>	ILE	10-bit resolution	$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$			$\pm 4.0$	LSB
Differential linearity error <sup>Note 1</sup>	DLE	10-bit resolution	$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$			$\pm 2.0$	LSB
Analog input voltage	$V_{AIN}$	ANI0 to ANI14		0		$V_{DD}$	V
		ANI16 to ANI26		0		$EV_{DD0}$	V
		Internal reference voltage output ( $2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$ , HS (high-speed main) mode)		$V_{BGR}$ <sup>Note 3</sup>			V
		Temperature sensor output voltage ( $2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$ , HS (high-speed main) mode)		$V_{TMPS25}$ <sup>Note 3</sup>			V

**Notes** 1. Excludes quantization error ( $\pm 1/2$  LSB).

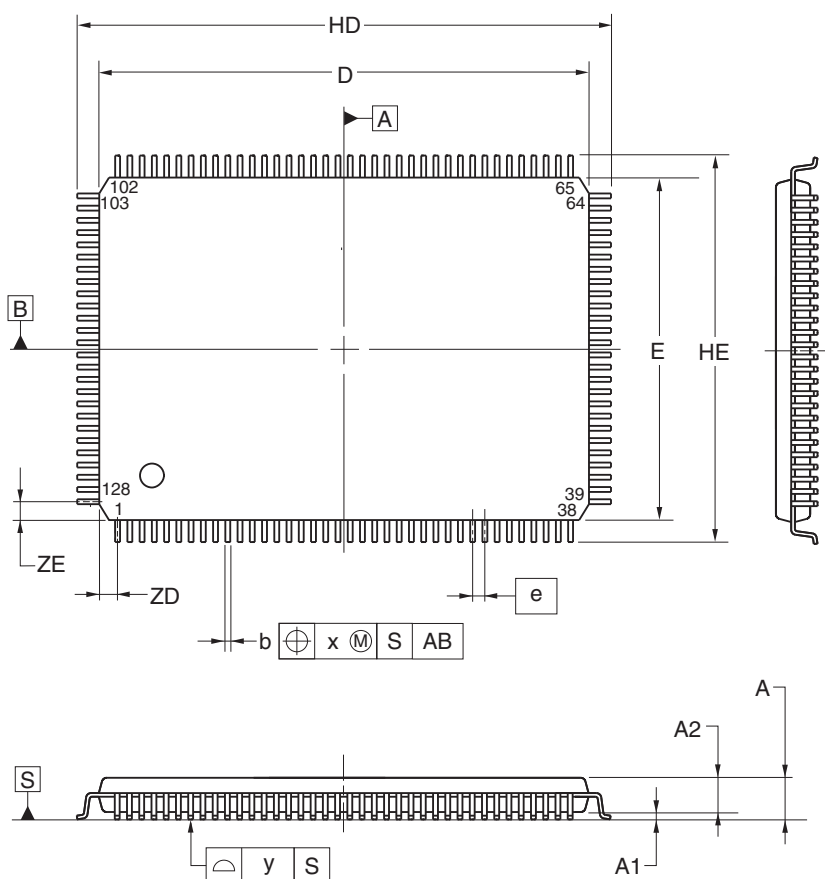
2. This value is indicated as a ratio (%FSR) to the full-scale value.

3. Refer to **3.6.2 Temperature sensor/internal reference voltage characteristics**.

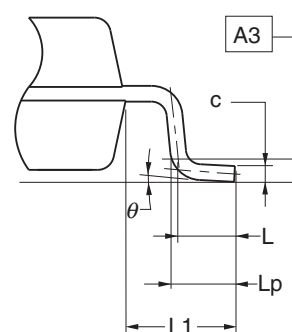
## 4.14 128-pin Products

R5F100SHAFB, R5F100SJAFB, R5F100SKAFB, R5F100SLAFB  
 R5F101SHAFB, R5F101SJAFB, R5F101SKAFB, R5F101SLAFB  
 R5F100SHDFB, R5F100SJDFB, R5F100SKDFB, R5F100SLDFB  
 R5F101SHDFB, R5F101SJDFB, R5F101SKDFB, R5F101SLDFB

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LFQFP128-14x20-0.50	PLQP0128KD-A	P128GF-50-GBP-1	0.92



detail of lead end



(UNIT:mm)

ITEM	DIMENSIONS
D	20.00±0.20
E	14.00±0.20
HD	22.00±0.20
HE	16.00±0.20
A	1.60 MAX.
A1	0.10±0.05
A2	1.40±0.05
A3	0.25
b	0.22±0.05
c	0.145 <sup>+0.055</sup> <sub>-0.045</sub>
L	0.50
Lp	0.60±0.15
L1	1.00±0.20
θ	3° <sup>+5°</sup> <sub>-3°</sub>
e	0.50
x	0.08
y	0.08
ZD	0.75
ZE	0.75

Rev.	Date	Description	
		Page	Summary
3.00	Aug 02, 2013	118	Modification of table in 2.6.2 Temperature sensor/internal reference voltage characteristics
		118	Modification of table and note in 2.6.3 POR circuit characteristics
		119	Modification of table in 2.6.4 LVD circuit characteristics
		120	Modification of table of LVD Detection Voltage of Interrupt & Reset Mode
		120	Renamed to 2.6.5 Power supply voltage rising slope characteristics
		122	Modification of table, figure, and remark in 2.10 Timing Specs for Switching Flash Memory Programming Modes
		123	Modification of caution 1 and description
		124	Modification of table and remark 3 in Absolute Maximum Ratings ( $T_A = 25^\circ\text{C}$ )
		126	Modification of table, note, caution, and remark in 3.2.1 X1, XT1 oscillator characteristics
		126	Modification of table in 3.2.2 On-chip oscillator characteristics
		127	Modification of note 3 in 3.3.1 Pin characteristics (1/5)
		128	Modification of note 3 in 3.3.1 Pin characteristics (2/5)
		133	Modification of notes 1 and 4 in (1) Flash ROM: 16 to 64 KB of 20- to 64-pin products (1/2)
		135	Modification of notes 1, 5, and 6 in (1) Flash ROM: 16 to 64 KB of 20- to 64-pin products (2/2)
		137	Modification of notes 1 and 4 in (2) Flash ROM: 96 to 256 KB of 30- to 100-pin products (1/2)
		139	Modification of notes 1, 5, and 6 in (2) Flash ROM: 96 to 256 KB of 30- to 100-pin products (2/2)
		140	Modification of (3) Peripheral Functions (Common to all products)
		142	Modification of table in 3.4 AC Characteristics
		143	Addition of Minimum Instruction Execution Time during Main System Clock Operation
		143	Modification of figure of AC Timing Test Points
		143	Modification of figure of External System Clock Timing
		145	Modification of figure of AC Timing Test Points
		145	Modification of description, note 1, and caution in (1) During communication at same potential (UART mode)
		146	Modification of description in (2) During communication at same potential (CSI mode)
		147	Modification of description in (3) During communication at same potential (CSI mode)
		149	Modification of table, note 1, and caution in (4) During communication at same potential (simplified I <sup>2</sup> C mode)
		151	Modification of table, note 1, and caution in (5) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (1/2)
		152 to 154	Modification of table, notes 2 to 6, caution, and remarks 1 to 4 in (5) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (2/2)
		155	Modification of table in (6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (1/3)
		156	Modification of table and caution in (6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (2/3)
		157, 158	Modification of table, caution, and remarks 3 and 4 in (6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (3/3)
		160, 161	Modification of table and caution in (7) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode)

Rev.	Date	Description	
		Page	Summary
3.00	Aug 02, 2013	163	Modification of table in (8) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I <sup>2</sup> C mode) (1/2)
		164, 165	Modification of table, note 1, and caution in (8) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I <sup>2</sup> C mode) (2/2)
		166	Modification of table in 3.5.2 Serial interface IICA
		166	Modification of IICA serial transfer timing
		167	Addition of table in 3.6.1 A/D converter characteristics
		167, 168	Modification of table and notes 3 and 4 in 3.6.1 (1)
		169	Modification of description in 3.6.1 (2)
		170	Modification of description and note 3 in 3.6.1 (3)
		171	Modification of description and notes 3 and 4 in 3.6.1 (4)
		172	Modification of table and note in 3.6.3 POR circuit characteristics
		173	Modification of table of LVD Detection Voltage of Interrupt & Reset Mode
		173	Modification from Supply Voltage Rise Time to 3.6.5 Power supply voltage rising slope characteristics
		174	Modification of 3.9 Dedicated Flash Memory Programmer Communication (UART)
		175	Modification of table, figure, and remark in 3.10 Timing Specs for Switching Flash Memory Programming Modes
3.10	Nov 15, 2013	123	Caution 4 added.
		125	Note for operating ambient temperature in 3.1 Absolute Maximum Ratings deleted.
3.30	Mar 31, 2016		Modification of the position of the index mark in 25-pin plastic WFLGA (3 × 3 mm, 0.50 mm pitch) of 1.3.3 25-pin products
			Modification of power supply voltage in 1.6 Outline of Functions [20-pin, 24-pin, 25-pin, 30-pin, 32-pin, 36-pin products]
			Modification of power supply voltage in 1.6 Outline of Functions [40-pin, 44-pin, 48-pin, 52-pin, 64-pin products]
			Modification of power supply voltage in 1.6 Outline of Functions [80-pin, 100-pin, 128-pin products]
			<del>ACK</del> corrected to ACK
			<del>ACK</del> corrected to ACK

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